

Features

512Kx32 bit CMOS Static

Random Access Memory

- Access Times: 15, 17 and 20ns
- Individual Byte Selects
- Fully Static, No Clocks
- TTL Compatible I/O

High Density Package

- 72 Pin ZIP, No. 173
- 72 lead SIMM, No. 174
- Common Data Inputs and Outputs

Single +3.3V ($\pm 10\%$) Supply Operation

512Kx32 Static RAM

CMOS, High Speed Module

The EDI8G32512V is a high speed 16 megabit Static RAM module organized as 512K words by 32 bits. This module is constructed from four 512Kx8 Static RAMs in SOJ packages on an epoxy laminate (FR4) board.

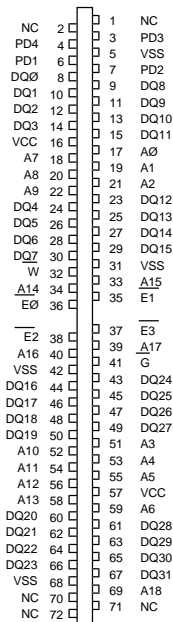
Four chip enables ($\overline{E0}$ -E3) are used to independently enable the four bytes. Reading or writing can be executed on individual bytes or any combination of multiple bytes through proper use of selects.

The EDI8G32512V is offered in gold plated 72 pin ZIP and 72 lead SIMM packages, which enable 16 megabits of memory to be placed in less than 1.3 square inches of board space.

All inputs and outputs are TTL compatible and operate from a single 3.3V supply. Fully asynchronous circuitry requires no clocks or refreshing for operation and provides equal access and cycle times for ease of use.

Pins PD1- PD4, are used to identify module memory density in applications where alternate modules can be interchanged.

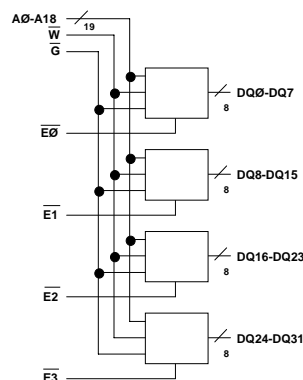
Pin Configurations and Block Diagram



PD1, PD2, PD4 = Open
PD3 = VSS

Pin Names

A0-A18	Address Inputs
$\overline{E0}$ -E3	Chip Enables
\overline{W}	Write Enable
\overline{G}	Output Enable
DQ0-DQ31	Common Data Input/Output
VCC	Power (+3.3V $\pm 10\%$)
VSS	Ground
NC	No Connection



Absolute Maximum Ratings

Voltage on any pin relative to VSS	-0.5V to 4.6V
Operating Temperature TA (Ambient)	
Commercial	0°C to +70°C
Storage Temperature, Plastic	-55°C to +125°C
Power Dissipation	2.5 Watts
Output Current	20 mA

*Stress greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions greater than those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Recommended DC Operating Conditions

Parameter	Sym	Min	Typ	Max	Units
Supply Voltage	VCC	3.0	3.3	3.6	V
Supply Voltage	VSS	0	0	0	V
Input High Voltage	VIH	2.2	--	Vcc +0.3	V
Input Low Voltage	VIL	-0.3	--	0.8	V

AC Test Conditions

Input Pulse Levels	VSS to 3.0V
Input Rise and Fall Times	5ns
Input and Output Timing Levels	1.5V
Output Load	1TTL, CL = 30pF

(note: For TEHQZ,TGHOZ and TWLOZ, CL = 5pF)

DC Electrical Characteristics

Parameter	Sym	Conditions	Min	Typ*	Max	Units
Operating Power Supply Current	ICC1	$\bar{W}, \bar{E} = VIL, I/O = 0mA, \text{Min Cycle}$			640	mA
Standby (TTL) Power Supply Current	ICC2	$\bar{E} \geq VIH, \bar{VIN} \leq VIL \text{ or } \bar{VIN} \geq VIH$			200	mA
Full Standby Power Supply Current	ICC3	$\bar{E} \geq VCC-0.2V$			40	mA
CMOS		$VIN \geq VCC-0.2V \text{ or } \bar{VIN} \leq 0.2V$				
Input Leakage Current	ILI	$VIN = 0V \text{ to } VCC$	--	--	±20	µA
Output Leakage Current	ILO	$V I/O = 0V \text{ to } VCC$	--	--	±20	µA
Output High Voltage	VOH	$IOH = -4.0mA$	2.4	--	--	V
Output Low Voltage	VOL	$IOL = 8.0mA$	--	--	0.4	V

*Typical: TA = 25°C, VCC = 5.0V

Truth Table

\bar{E}	\bar{W}	\bar{G}	Mode	Output	Power
H	X	X	Standby	HIGH Z	ICC2/ICC3
L	H	L	Read	DOUT	ICC1
L	L	X	Write	DIN	ICC1
			Output		
L	H	H	Deselect	HIGH Z	ICC1

Capacitance

(f=1.0MHz, VIN=VCC or VSS)

Parameter	Sym	Max	Unit
Address Lines	CI	45	pF
Data Lines	CD/Q	20	pF
Chip Enable Line	CC	20	pF
Write Line	CN	45	pF

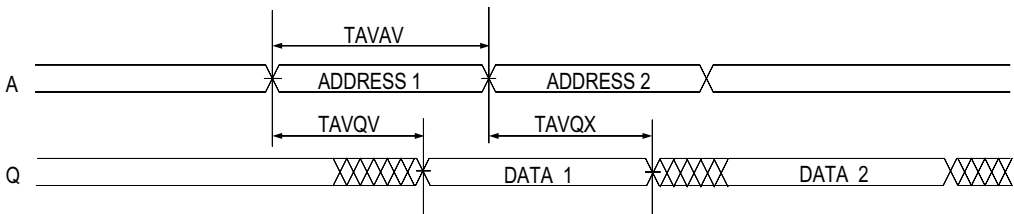
These parameters are sampled, not 100% tested.

AC Characteristics Read Cycle

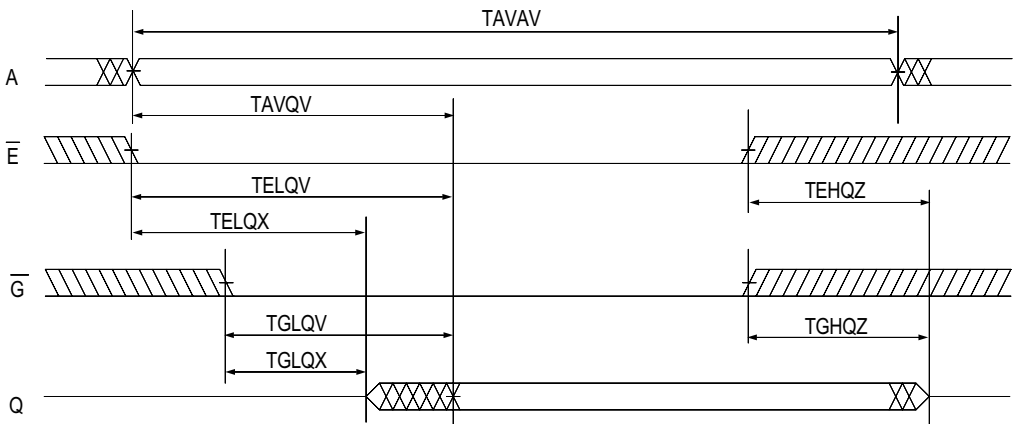
Parameter	Symbol		15ns		17ns		20ns	
	JEDEC	Alt.	Min	Max	Min	Max	Min	Max
Read Cycle Time	TAVAV	TRC	15		17		20	
Address Access Time	TAVQV	TAA		15		17		20
Chip Enable Access	TELOV	TACS		15		17		20
Chip Enable to Output in Low Z (1)	TELOX	TCLZ	3		3		3	
Chip Disable to Output in High Z (1)	TEHOZ	TCHZ		7		7		10
Output Hold from Address Change	TAVQX	TOH	3		3		3	
Output Enable to Output Valid	TGLOV	TOE		7		7		8
Output Enable to Output in Low Z (1)	TGLOX	TOLZ	0		0		0	
Output Disable to Output in High Z(1)	TGHQZ	TOHZ		7		7		8

Notes 1. Parameter guaranteed, but not tested.

Read Cycle 1 - \overline{W} High, \overline{G} , \overline{E} Low



Read Cycle 2 - \overline{W} High

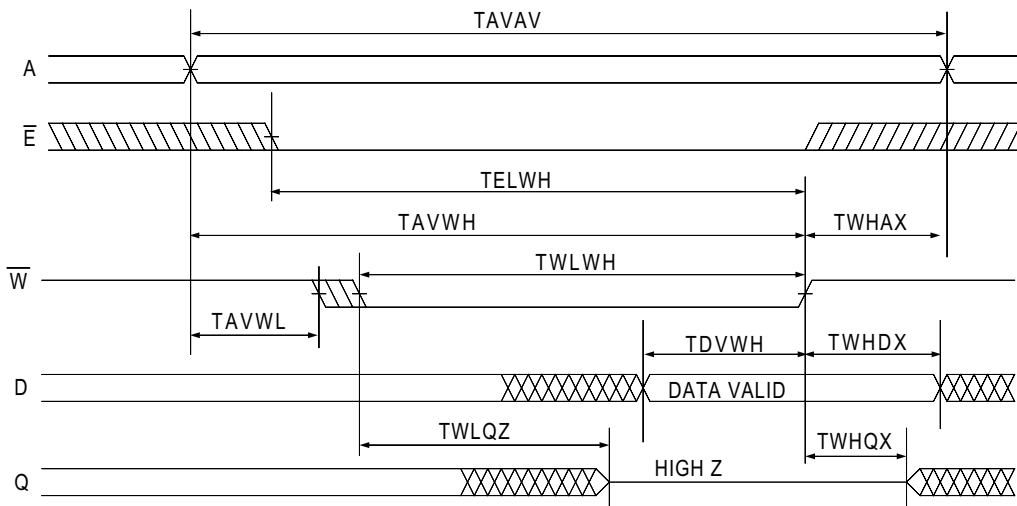


AC Characteristics Write Cycle

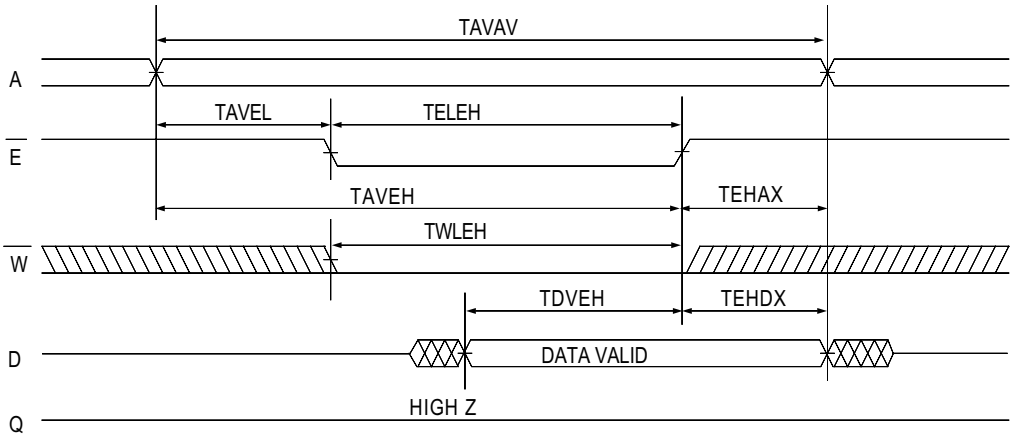
Parameter	Symbol		15ns		17ns		20ns	
	JEDEC	Alt.	Min	Max	Min	Max	Min	Max
Write Cycle Time	TAVAV	TWC	15		17		20	
Chip Enable to End of Write	TELWH	TCW	10		12		15	
	TWLEH	TCW	10		12		15	
Address Setup Time	TAVWL	TAS	0		0		0	
	TAVEL	TAS	0		0		0	
Address Valid to End of Write	TAVWH	TAW	10		12		15	
	TAVEH	TAW	10		12		15	
Write Pulse Width	TWLWH	TWP	10		12		15	
	TELEH	TWP	10		12		15	
Write Recovery Time	TWHAX	TWR	0		0		0	
	TEHAX	TWR	0		0		0	
Data Hold Time	TWHDX	TDH	0		0		0	
	TEHDX	TDH	0		0		0	
Write to Output in High Z (1)	TWLQZ	TWHZ	0	7	0	8	0	8
Data to Write Time	TDVWH	TDW	7		8		9	
	TDVEH	TDW	7		8		9	
Output Active from End of Write (1)	TWHQX	TWLZ	2		2		3	

Notes: 1. Parameter guaranteed, but not tested.

Write Cycle 1 - W Controlled



Write Cycle 2 - \bar{E} Controlled



Ordering Information

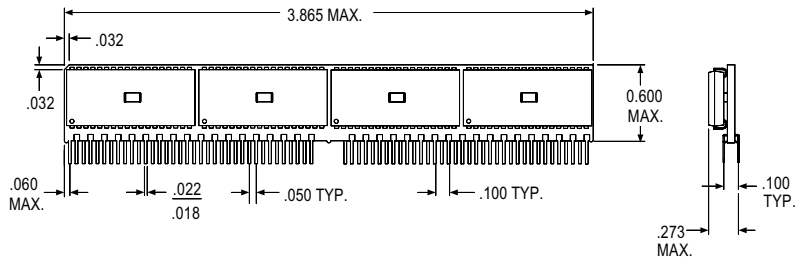
Part Number	Speed (ns)	Package No.
EDI8G32512V15MMC	15	174
EDI8G32512V17MMC	17	174
EDI8G32512V20MMC	20	174

Part Number	Speed (ns)	Package No.
EDI8G32512V15MZC	15	173
EDI8G32512V17MZC	17	173
EDI8G32512V20MZC	20	173

Package Description

Package No. 173
72 Pin ZIP

(Gold Plated Leads)

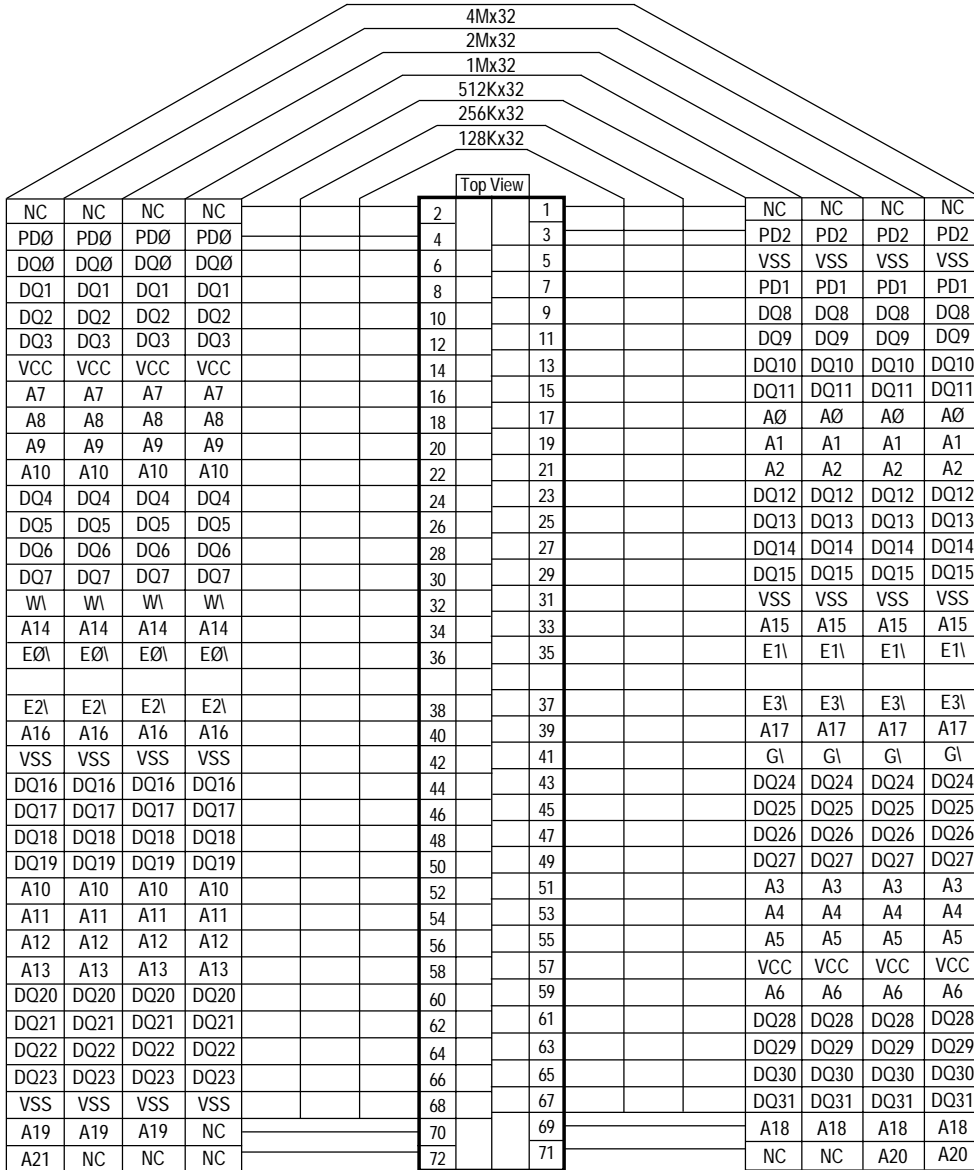


Package No. 174
72 lead SIMM

(Gold Plated Contacts)



X32 Pinout Map for 72 pin ZIP Package Configurations



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